

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A thin-layer LED chip[[(5)]] comprising an epitaxial layer sequence[[(6)]] that is disposed on a carrier element[[(2)]] and comprises an electromagnetic-radiation-generating active region[[(8)]], and a reflective layer[[(3)]] that is disposed on a principal surface of said epitaxial layer sequence[[(6)]] facing toward said carrier element[[(2)]] and reflects at least a portion of the electromagnetic radiation generated in said epitaxial layer sequence[[(6)]] back thereinto, ~~characterized in that~~ wherein-disposed on a radiation extraction surface[[(7)]] of said epitaxial layer sequence[[(6)]] facing away from said carrier element[[(2)]] is a structured layer[[(1)]] containing a glass material and exhibiting a structure that includes mutually adjacent protuberances[[(5)]] that taper away from said radiation extraction surface[[(7)]] and have a lateral grid size that is smaller than one wavelength of an electromagnetic radiation emitted from said epitaxial layer sequence[[(6)]].
2. (Currently Amended) The thin-layer LED chip as in claim 1, ~~characterized in that~~ wherein the refractive index of said layer[[(1)]] lies between the refractive index of a material of a side of said epitaxial layer sequence[[(6)]] adjacent said radiation extraction surface[[(7)]] and the refractive index of a medium intended as an ambient for said thin-layer LED chip[[(5)]].
3. (Currently Amended) The thin-layer LED chip as in claim 1[[or 2]], ~~characterized in that~~ wherein-said structure comprises protuberances[[(5)]] that are largely periodically arranged.
4. (Currently Amended) The thin-layer LED chip as in ~~one of claims 1 to 3~~ claim 1, ~~characterized in that~~ said protuberances[[(5)]] are convexly curved as viewed from the outside.

5. (Currently Amended) The thin-layer LED chip as in ~~one of claims 1 to 4~~ claim 1, characterized in that wherein said glass material is a spin-on glass.

6. (Currently Amended) The thin-layer LED chip as in ~~one of claims 1 to 5~~ claim 1, characterized in that the height of said protuberances[[(5)]] in the direction away from said radiation extraction surface[[(7)]] is smaller than one wavelength of an electromagnetic radiation emitted from said epitaxial layer sequence[[(6)]].

7. (Currently Amended) A method for making a thin-layer LED chip[[(5)]] comprising an epitaxial layer sequence[[(6)]] that is disposed on a carrier element[[(2)]] and contains an electromagnetic-radiation-generating active region[[(8)]]], and a reflective layer[[(3)]] that is disposed on a principal surface of said epitaxial layer sequence[[(6)]] facing toward said carrier element[[(2)]] and reflects at least a portion of the electromagnetic radiation generated in said epitaxial layer sequence[[(6)]] back thereinto, characterized in that wherein said epitaxial layer sequence[[(6)]] disposed on said carrier element[[(2)]] is prepared, a layer[[(1)]] containing a glass material is applied to a radiation extraction surface[[(7)]] of said epitaxial layer sequence [[(6)]]facing away from said carrier element[[(2)]], and a structure is introduced into at least a portion of said layer[[(1)]]], said structure including mutually adjacent protuberances[[(5)]] that taper in the direction away from said radiation extraction surface and have a lateral grid size that is smaller than one wavelength of an electromagnetic radiation emitted from said epitaxial layer sequence[[(6)]].

8. (Currently Amended) The method as in claim 7, characterized in that wherein-said layer[[(1)]] is fabricated by applying a still-molten spin-on glass to said radiation extraction surface[[(7)]] and thermally treating said spin-on glass such that it hardens and densifies.

9. (Currently Amended) The method as in claim 8, characterized in that wherein the spin-on glass is applied by spin-coating and/or printing.

10. (Currently Amended) The method as in ~~one of claims 7 to 9~~ claim 7, characterized in that wherein said structure is introduced into said layer[[(1)]] by grayscale lithography[[(6)]].

11. (Currently Amended) The method as in ~~one of claims 7 to 10~~ claim 7, characterized in that wherein-said structure is introduced in such fashion that it comprises periodically arranged protuberances[[(5)]].

12. (Currently Amended) The method as in ~~one of claims 7 to 11~~ claim 7, characterized in that wherein-the refractive index of said layer[[(1)]] lies between the refractive index of a material of a side of said epitaxial layer sequence (6) facing toward said radiation extraction surface[[(7)]] and the refractive index of a medium intended as an ambient for said thin-layer LED chip[[(5)]].

13. (Currently Amended) The method as in ~~one of claims 7 to 12~~ claim 7, characterized in that wherein said structure is introduced in such fashion that the height of said protuberances[[(5)]] in the direction away from said radiation extraction surface[[(7)]] is smaller than one wavelength of an electromagnetic radiation emitted from said epitaxial layer sequence[[(6)]].

14. (New) The thin-layer led chip as in claim 2, wherein said structure comprises protuberances that are largely periodically arranged.